

TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

524,288-WORD BY 8-BIT CMOS STATIC RAM

**DESCRIPTION**

The TC55V8512J/FT is a 4,194,304-bit high-speed static random access memory (SRAM) organized as 524,288 words by 8 bits. Fabricated using CMOS technology and advanced circuit techniques to provide high speed, it operates from a single 3.3 V power supply. Chip enable ( $\overline{CE}$ ) can be used to place the device in a low-power mode, and output enable ( $\overline{OE}$ ) provides fast memory access. This device is well suited to cache memory applications where high-speed access and high-speed storage are required. All inputs and outputs are directly LVTTL compatible. The TC55V8512J/FT is available in plastic 36-pin SOJ and 44-pin TSOP with 400mil width for high density surface assembly.

**FEATURES**

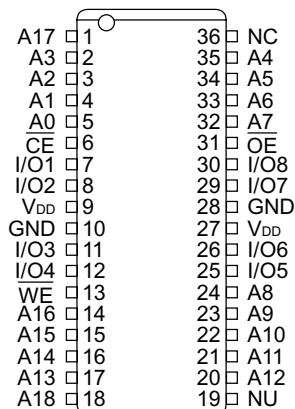
- Fast access time (the following are maximum values)  
TC55V8512J/FT-12:12 ns  
TC55V8512J/FT-15:15 ns
- Low-power dissipation  
(the following are maximum values)
- Single power supply voltage of 3.3 V  $\pm$  0.3 V
- Fully static operation
- All inputs and outputs are LVTTL compatible
- Output buffer control using  $\overline{OE}$
- Package:  
SOJ36-P-400-1.27 (J) (Weight: 1.35 g typ)  
TSOP II44-P-400-0.80 (FT) (Weight: 0.45 g typ)

Cycle Time	12	15	20	25	ns
Operation (max)	170	140	130	110	mA

Standby:4 mA (both devices)

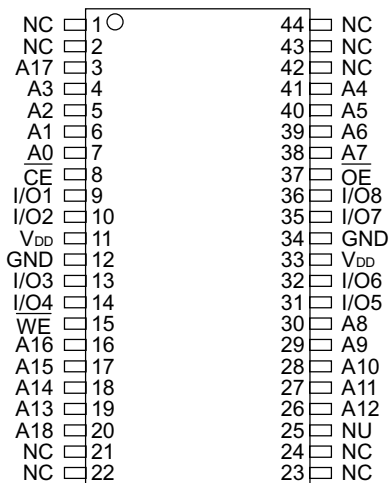
**PIN ASSIGNMENT (TOP VIEW)**

**36 PIN SOJ**



(TC55V8512J)

**44 PIN TSOP**

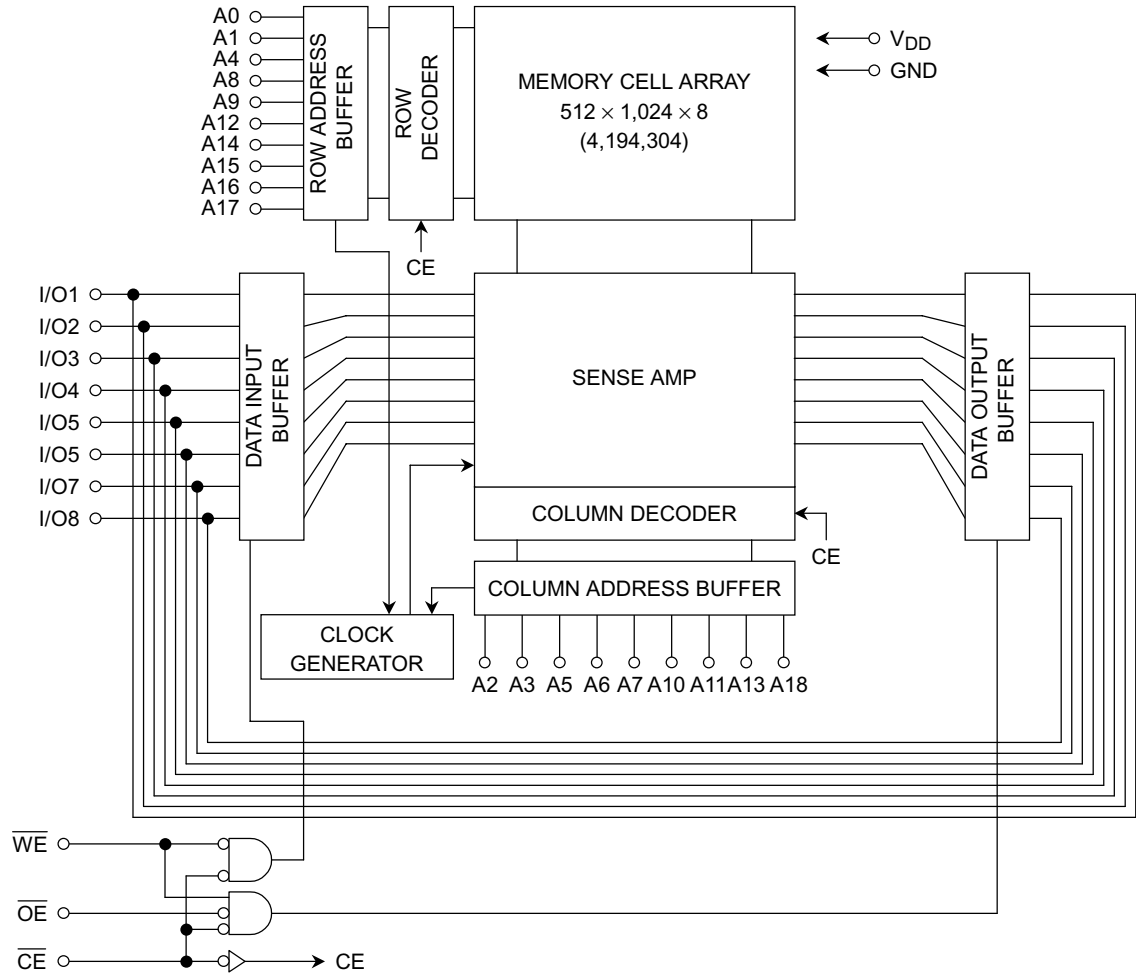


(TC55V8512FT)

**PIN NAMES**

A0 to A18	Address Inputs
I/O1 to I/O8	Data Inputs/Outputs
$\overline{CE}$	Chip Enable Input
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
V <sub>DD</sub>	Power (+3.3 V)
GND	Ground
NC	No Connection
NU	Not Usable (Input)

BLOCK DIAGRAM



MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT
V <sub>DD</sub>	Power Supply Voltage	-0.5 to 4.6	V
V <sub>IN</sub>	Input Terminal Voltage	-0.5* to 4.6	V
V <sub>I/O</sub>	Input/Output Terminal Voltage	-0.5* to V <sub>DD</sub> + 0.5**	V
P <sub>D</sub>	Power Dissipation	1.4	W
T <sub>solder</sub>	Soldering Temperature (10s)	260	°C
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
T <sub>opr</sub>	Operating Temperature	-10 to 85	°C

\*: -1.5 V with a pulse width of 20%·t<sub>RC</sub> min (4 ns max)

\*\*: V<sub>DD</sub> + 1.5 V with a pulse width of 20%·t<sub>RC</sub> min (4 ns max)

DC RECOMMENDED OPERATING CONDITIONS (Ta = 0° to 70°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
V <sub>DD</sub>	Power Supply Voltage	3.0	3.3	3.6	V
V <sub>IH</sub>	Input High Voltage	2.0	—	V <sub>DD</sub> + 0.3**	V
V <sub>IL</sub>	Input Low Voltage	-0.3*	—	0.8	V

\*: -1.0 V with a pulse width of 20%·t<sub>RC</sub> min (4 ns max)

\*\*: V<sub>DD</sub> + 1.0 V with a pulse width of 20%·t<sub>RC</sub> min (4 ns max)

## DC CHARACTERISTICS (Ta = 0° to 70°C, VDD = 3.3 V ± 0.3 V)

SYMBOL	PARAMETER	TEST CONDITION		MIN	TYP	MAX	UNIT
I <sub>IL</sub>	Input Leakage Current (Except NU pin)	V <sub>IN</sub> = 0 to V <sub>DD</sub>		−1	—	1	μA
I <sub>LO</sub>	Output Leakage Current	$\overline{CE} = V_{IH}$ or $\overline{WE} = V_{IL}$ or $\overline{OE} = V_{IH}$ , V <sub>OUT</sub> = 0 to V <sub>DD</sub>		−1	—	1	μA
I <sub>I</sub> (NU)	Input Current (NU pin)	V <sub>IN</sub> = 0 to 0.8 V		−1	—	20	μA
		V <sub>IN</sub> = 0 to 0.2 V		−1	—	1	
V <sub>OH</sub>	Output High Voltage	I <sub>OH</sub> = −2 mA		2.4	—	—	V
		I <sub>OH</sub> = −100 μA		V <sub>DD</sub> − 0.2	—	—	
V <sub>OL</sub>	Output Low Voltage	I <sub>OL</sub> = 2 mA		—	—	0.4	
		I <sub>OL</sub> = 100 μA		—	—	0.2	
I <sub>DDO</sub>	Operating Current	$\overline{CE} = V_{IL}$ , I <sub>OUT</sub> = 0 mA, $\overline{OE} = V_{IH}$ , Other Input = V <sub>IH</sub> /V <sub>IL</sub>	t <sub>cycle</sub> = 12 ns	—	—	170	mA
			t <sub>cycle</sub> = 15 ns	—	—	140	
			t <sub>cycle</sub> = 20 ns	—	—	130	
			t <sub>cycle</sub> = 25 ns	—	—	110	
I <sub>DDS1</sub>	Standby Current	$\overline{CE} = V_{IH}$ , Other Input = V <sub>IH</sub> or V <sub>IL</sub>		—	—	50	mA
I <sub>DDS2</sub>		$\overline{CE} = V_{DD} - 0.2$ V, Other Input = V <sub>DD</sub> − 0.2 V or 0.2 V		—	—	4	

## CAPACITANCE (Ta = 25°C, f = 1.0 MHz)

SYMBOL	PARAMETER	TEST CONDITION	MAX	UNIT
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = GND	6	pF
C <sub>I/O</sub>	Input/Output Capacitance	V <sub>I/O</sub> = GND	8	pF

Note: This parameter is periodically sampled and is not 100% tested.

## OPERATING MODE

MODE	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O1 to I/O8	POWER
Read	L	L	H	Output	I <sub>DDO</sub>
Write	L	*	L	Input	I <sub>DDO</sub>
Outputs Disable	L	H	H	High Impedance	I <sub>DDO</sub>
Standby	H	*	*	High Impedance	I <sub>DDS</sub>

\* : Don't care

Note: The NU pin must be left unconnected or tied to GND or a voltage level of less than 0.8 V.  
You must not apply a voltage of more than 0.8 V to the NU.

## AC CHARACTERISTICS (Ta = 0° to 70°C (See Note 1), VDD = 3.3 V ± 0.3 V)

### READ CYCLE

SYMBOL	PARAMETER	TC55V8512J/FT				UNIT
		-12		-15		
		MIN	MAX	MIN	MAX	
t <sub>RC</sub>	Read Cycle Time	12	—	15	—	ns
t <sub>ACC</sub>	Address Access Time	—	12	—	15	
t <sub>CO</sub>	Chip Enable Access Time	—	12	—	15	
t <sub>OE</sub>	Output Enable Access Time	—	6	—	8	
t <sub>OH</sub>	Output Data Hold Time from Address Change	3	—	4	—	
t <sub>COE</sub>	Output Enable Time from Chip Enable	3	—	4	—	
t <sub>OEE</sub>	Output Enable Time from Output Enable	1	—	1	—	
t <sub>COD</sub>	Output Disable Time from Chip Enable	—	7	—	8	
t <sub>ODO</sub>	Output Disable Time from Output Enable	—	7	—	8	

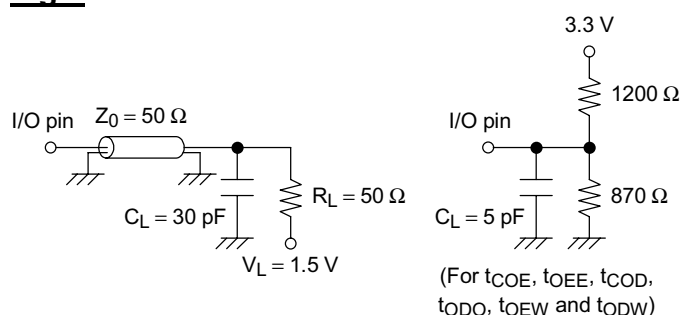
### WRITE CYCLE

SYMBOL	PARAMETER	TC55V8512J/FT				UNIT
		-12		-15		
		MIN	MAX	MIN	MAX	
t <sub>WC</sub>	Write Cycle Time	12	—	15	—	ns
t <sub>WP</sub>	Write Pulse Width	8	—	9	—	
t <sub>CW</sub>	Chip Enable to End of Write	10	—	12	—	
t <sub>AW</sub>	Address Valid to End of Write	10	—	12	—	
t <sub>AS</sub>	Address Setup Time	0	—	0	—	
t <sub>WR</sub>	Write Recovery Time	0	—	0	—	
t <sub>DS</sub>	Data Setup Time	7	—	8	—	
t <sub>DH</sub>	Data Hold Time	0	—	0	—	
t <sub>OE<sub>W</sub></sub>	Output Enable Time from Write Enable	1	—	1	—	
t <sub>OD<sub>W</sub></sub>	Output Disable Time from Write Enable	—	7	—	8	

## AC TEST CONDITIONS

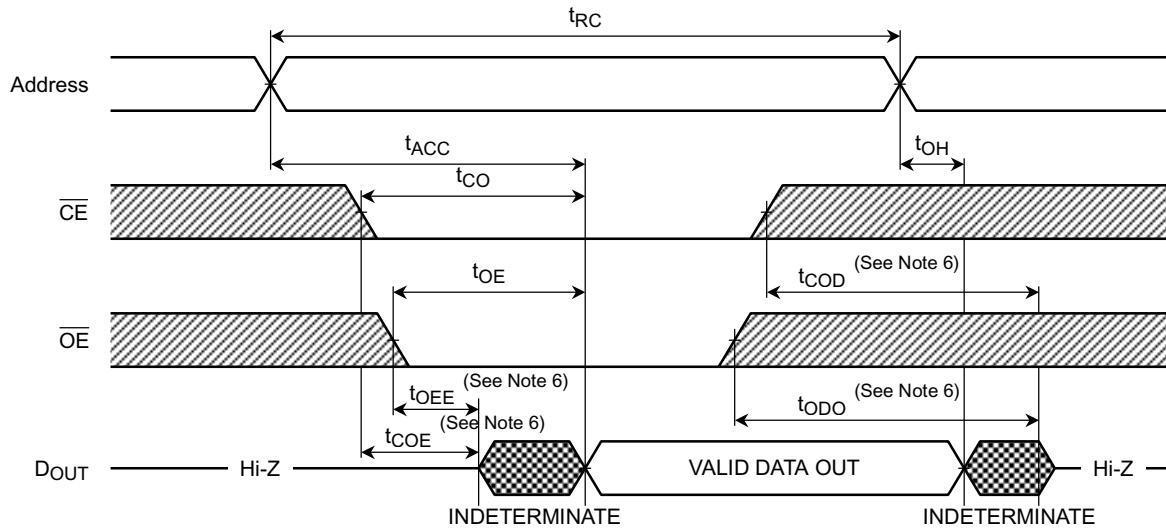
PARAMETER	TEST CONDITION
Input Pulse Level	3.0 V/ 0.0 V
Input Pulse Rise and Fall Time	2 ns
Input Timing Measurement Reference Level	1.5 V
Output Timing Measurement Reference Level	1.5 V
Output Load	Fig.1

**Fig.1**

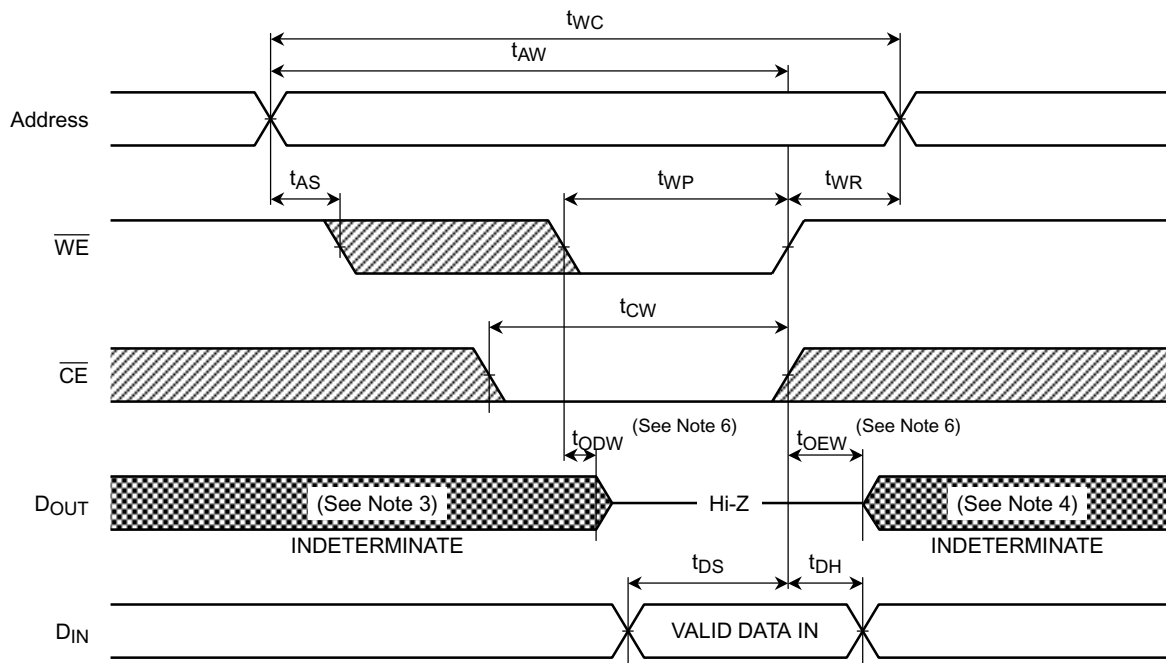


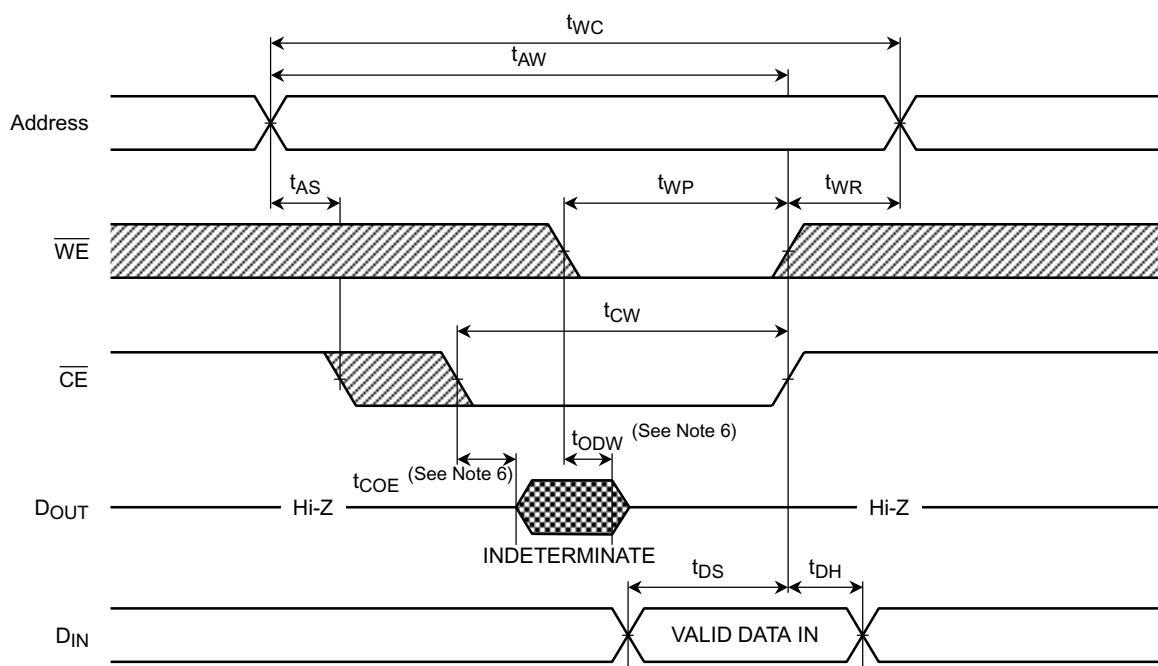
## TIMING DIAGRAMS

### READ CYCLE (See Note 2)



### WRITE CYCLE 1 ( $\overline{WE}$ CONTROLLED) (See Note 5)



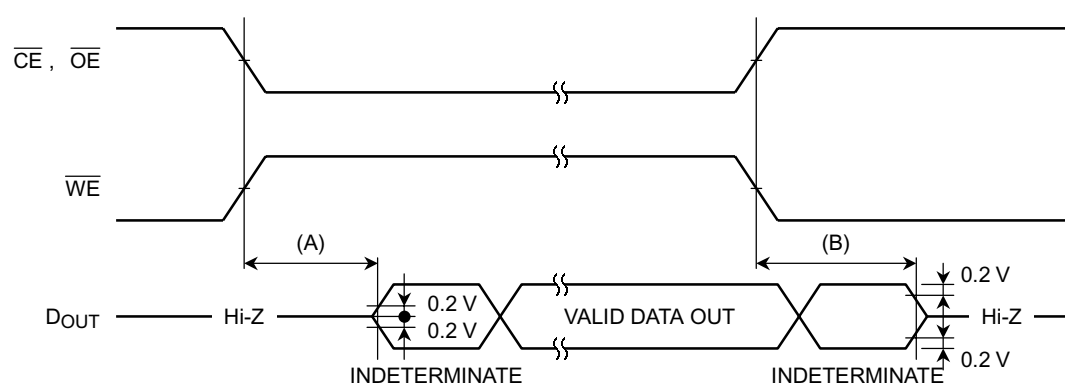
**WRITE CYCLE 2 ( $\overline{\text{CE}}$  CONTROLLED)** (See Note 5)


Note:

- (1) Operating temperature ( $T_a$ ) is guaranteed for transverse air flow exceeding 400 linear feet per minute.
- (2)  $\overline{WE}$  remains HIGH for the Read Cycle.
- (3) If  $\overline{CE}$  goes LOW coincident with or after  $\overline{WE}$  goes LOW, the outputs will remain at high impedance.
- (4) If  $\overline{CE}$  goes HIGH coincident with or before  $\overline{WE}$  goes HIGH, the outputs will remain at high impedance.
- (5) If  $\overline{OE}$  is HIGH during the write cycle, the outputs will remain at high impedance.
- (6) The parameters specified below are measured using the load shown in Fig.1.

(A)  $t_{COE}$ ,  $t_{OEE}$ ,  $t_{OE\overline{W}}$  ..... Output Enable Time

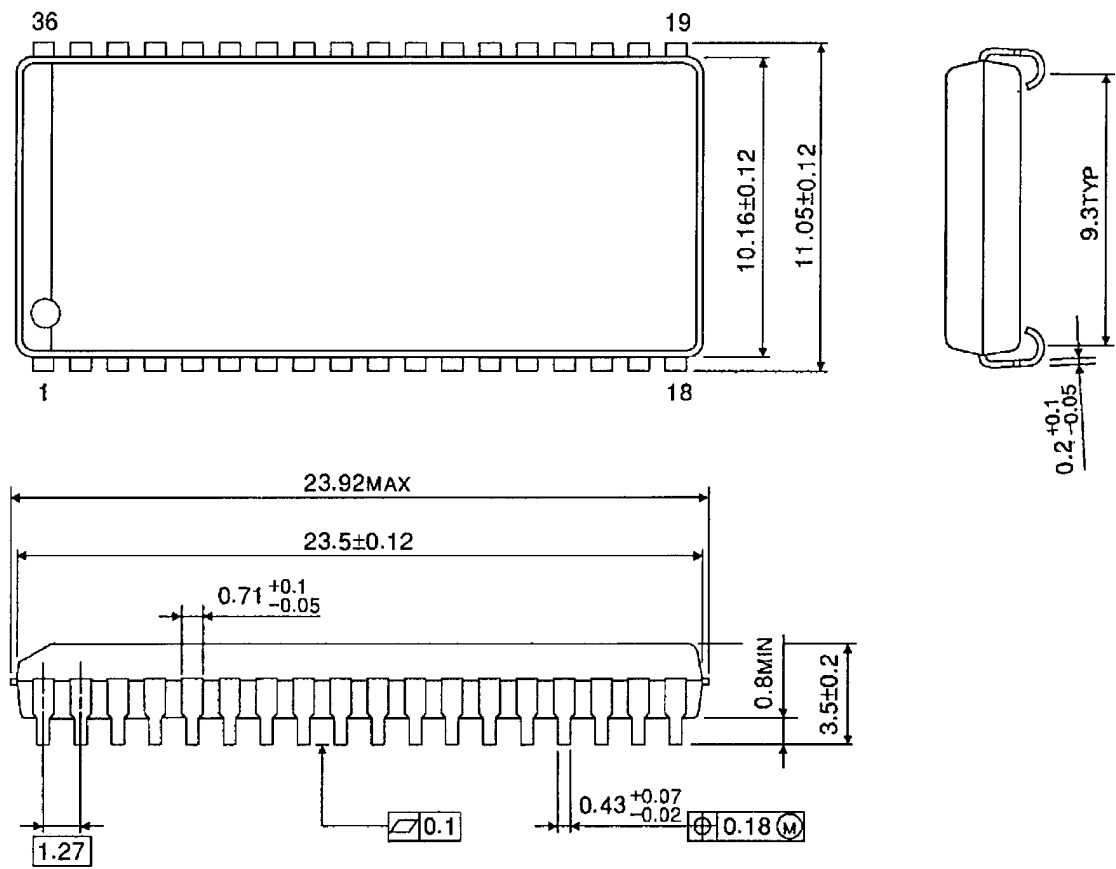
(B)  $t_{COD}$ ,  $t_{ODO}$ ,  $t_{OD\overline{W}}$  ..... Output Disable Time



PACKAGE DIMENSIONS

SOJ36-P-400-1.27

Unit : mm



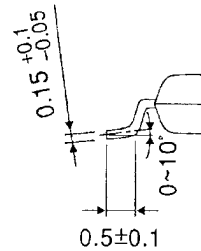
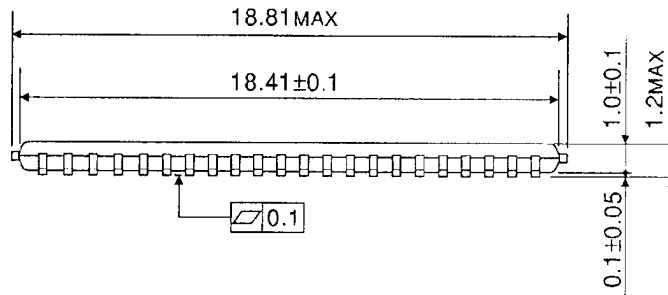
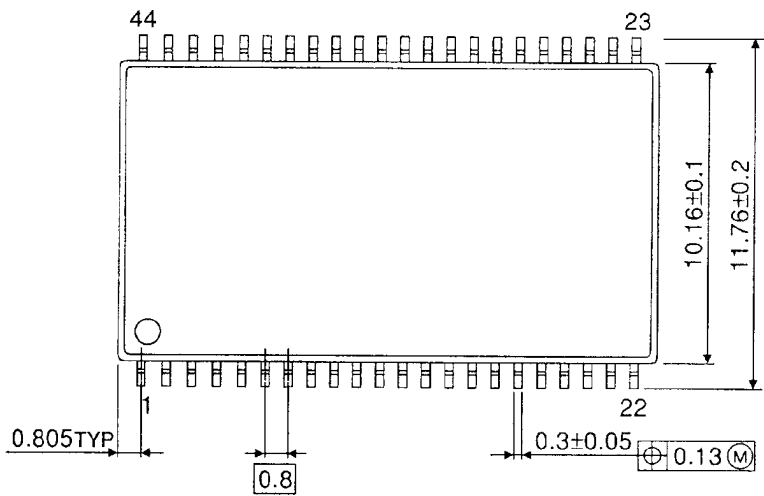
Weight: 1.35 g (typ)



PACKAGE DIMENSIONS

TSOP11 44-P-400-0.80

Unit : mm



Weight: 0.45 g (typ)

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